

Tool ID: 108  
Tool Location: 103

Equipment Information Sheet  
LPCVD Nitride - B4

**Manager:**  
**Backup:**

**Phil Infante**  
**Aaron Windsor**

**607-254-4926**  
**607-254-4831**

Calls to staff phones will be automatically forwarded to their cell phones during accessible hours. At other times leave a message or send them an email.

**SAFETY**

- The furnaces are run at elevated temperatures of 400-1200°C and use flammable, toxic, and corrosive gases.

**USAGE RESTRICTIONS**

- No changing of gas flows or process parameters without staff approval
- Max temperature of 800 C

**SCHEDULING/SIGN-UP RESTRICTIONS**

Minimum Tool Time: 90 minutes

- Reservation blocks greater than 8 hrs must be cleared by a MOS staff person prior to reserving the time

**MATERIALS COMPATIBILITY CATEGORY**

Tool Category 1E: Silicon Based Materials and Select Dielectrics	
Allowed	Not Allowed
Silicon Based Materials only	No Evaporated or Sputtered Films
Si, SiC, SiO <sub>2</sub> substrates	No Metal or Organic Films
All Furnace grown or deposited films	No Glass Substrates
PECVD Films	No III/V Compound Semiconductors
Select ALD dielectrics (SiO <sub>2</sub> , SiN, HfO <sub>2</sub> , HFN)	No High Vapor pressure materials
Spin on Glass and Spin on Dopants	Organic/Biology Molecules prepared-with or without Salt buffers

**High Vapor Pressure Metals and Compounds**are materials that have a vapor pressure above 1e-6 Torr at 400 C.

**Additional Material Restrictions and Exceptions**

- MOS CLEAN required prior to use
- Only use MOS designated holders, wands and tweezers

Last Updated: 03/20/2019